

# MICROWAVE POWER GaAs FET

# TIM7785-60SL

#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

### **FEATURES**

- ·BROAD BAND INTERNALLY MATCHED FET
- ·HIGH POWER

P1dB= 48.0dBm at 7.7GHz to 8.5GHz

·HIGH GAIN

G1dB= 6.0dB at 7.7GHz to 8.5GHz

**LOW INTERMODULATION DISTORTION** 

IM3(MIN.)= -42dBc at Pout= 36.5dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



# RF PERFORMANCE SPECIFICATIONS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	. VDS= 10V IDSset= 9.5A . f= 7.7 to 8.5GHz	dBm	47.0	48.0	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	5.0	6.0	_
Drain Current	IDS1		Α		13.2	15.0
Gain Flatness	ΔG		dB			±0.8
Power Added Efficiency	ηadd		%	_	36	_
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 36.5dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-42	-45	_
Drain Current	IDS2		Α	_	_	11.8
Channel Temperature Rise	ΔTch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C	_	_	100

Recommended Gate Resistance(Rg): 28 Ω

# **ELECTRICAL CHARACTERISTICS (Ta=25°C)**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 12.0A	S	_	20.0	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 200mA	V	-1.0	-1.8	-3.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	Α	_	38	_
Gate-Source Breakdown Voltage	VGSO	IGS= -1.0mA	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	0.6	0.8

- MICROWAVE SEMICONDUCTOR TECHNICAL DATA

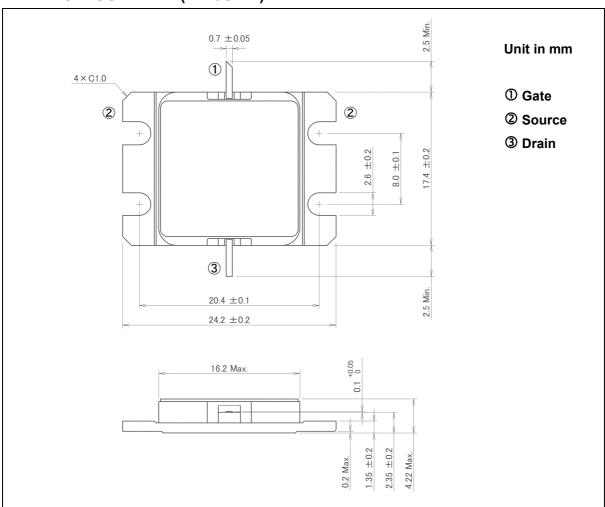
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# ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	20.0
Total Power Dissipation (Tc= 25°C)	PT	W	187.5
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

# PACKAGE OUTLINE (2-16G1B)



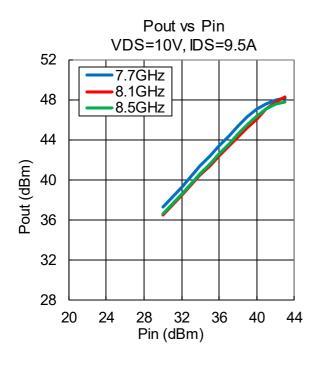
# HANDLING PRECAUTIONS FOR PACKAGE MODEL

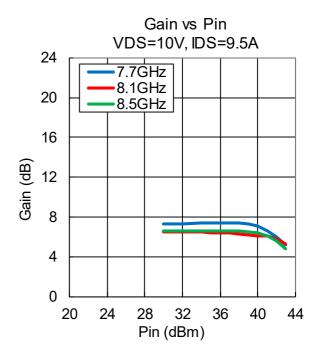
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

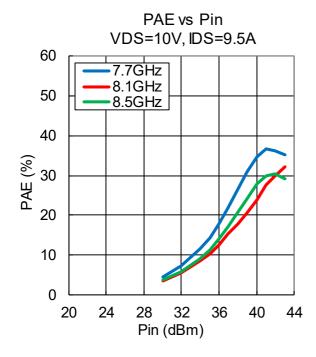
### **TYPICAL RF PERFORMANCE**

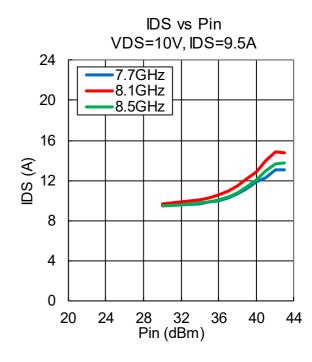
·Pout, Gain, PAE, IDS vs. Pin

VDS= 10 V, IDSset= 9.5 A, f= 7.7, 8.1, 8.5 GHz, Ta= +25 °C



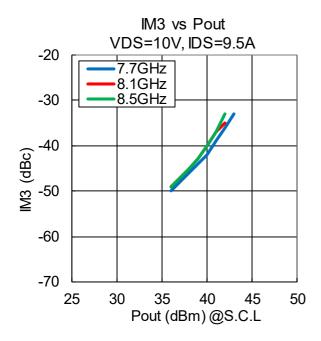


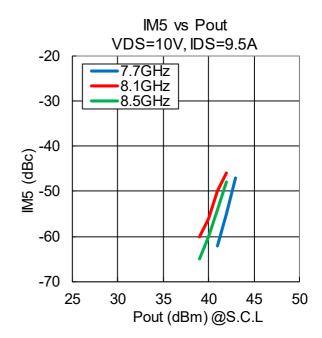




·IM3, IM5 vs. Pout

VDS= 10 V, IDSset= 9.5 A, f= 7.7, 8.1, 8.5 GHz,  $\Delta$ f= 5 MHz , Ta= +25  $^{\circ}$ C

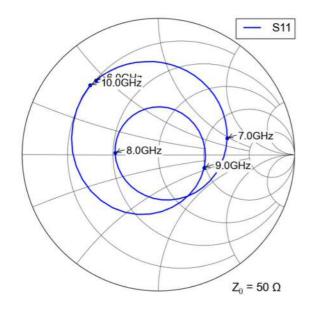


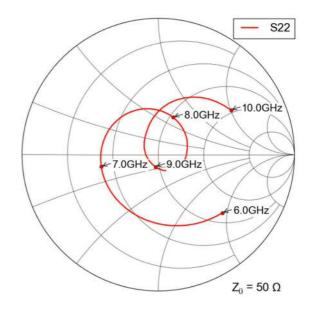


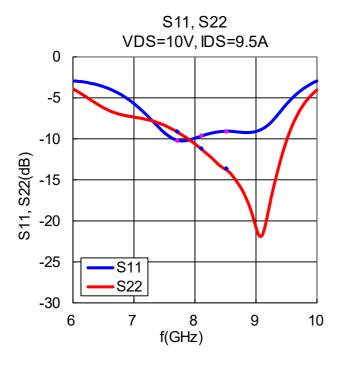


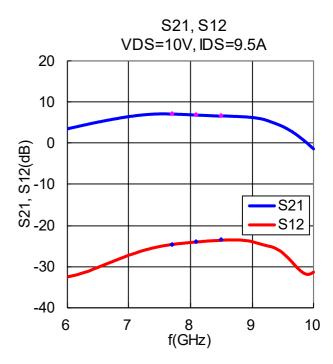
#### ·S-Parameters

VDS= 10 V, IDSset= 9.5 A, f= =6.0 to 10.0 GHz, Ta= +25  $^{\circ}$ C











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